

Patent Document Report

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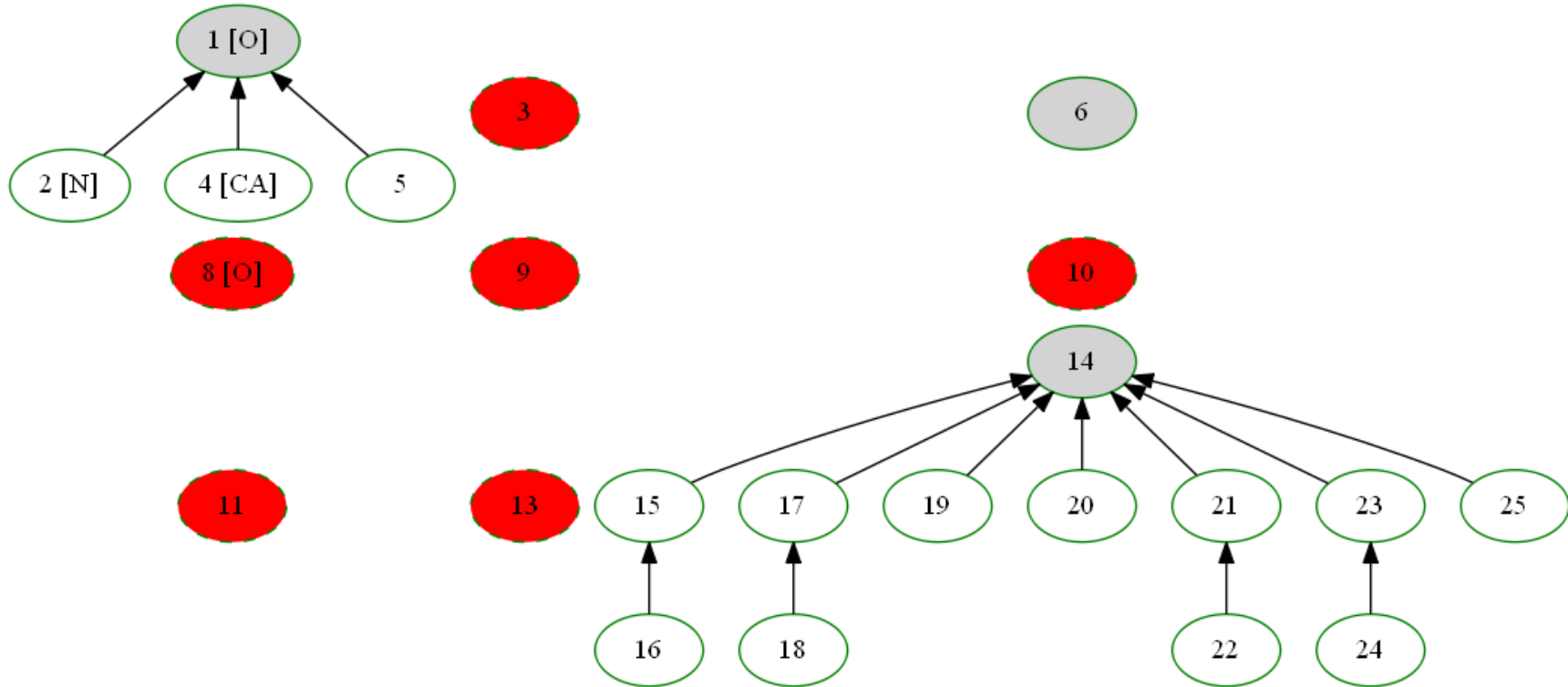
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TABLE OF CONTENTS

I.	Claims (Tree and Text)	3
II.	Claim Language Errors/Warnings	7
III.	Antecedents Errors/Warnings	15
IV.	Claim Terms without Explicit Support in the Specification	22
V.	Inconsistent Part Names/Numbers	24
VI.	Inconsistent Part Numbers in Figures	27
VII.	Inconsistent Acronyms	29
VIII.	Document Language Errors/Warnings	30

I. Claims (Tree and Text)

Note: The type of each claim is indicated by its color.¹ Independent claims are grey inside. Claims with invalid parent numbers are dotted. If present, status indicators will be provided in brackets next to the claim numbers.²



1. (Original) A method for forming a liquid crystal display including a thin film transistor, said method comprising the steps of:
depositing a first metal layer on a substrate;

¹ Claim type color legend: **Method/process**; **Apparatus/device**; **Composition**; **Article of manufacture**; **112(6)**; **Product by process**; **Jepson**

² Status indicator legend: [O]=“Original”; [PP]=“Previously Presented”; [CA]=“Currently Amended”; [N]=“New”; [X]=“Cancelled”; [W]=“Withdrawn”; [WA]=“Withdrawn and Amended”; [NE]=“Not Entered”

<p>depositing a second metal layer on said first metal layer opposite said substrate;</p> <p>patterning said first and second metal layers to provide a gate electrode on a TFT area of said substrate and to provide a gate pad on a pad area of said substrate;</p> <p>forming an insulating layer on said gate electrode and on said gate pad, and on said substrate;</p> <p>forming a semiconductor layer on said insulating layer opposite said gate electrode wherein said semiconductor layer includes a channel region opposite said gate electrode and first and second spaced apart source/drain regions separated by said channel region;</p> <p>forming first and second spaced apart metal source/drain electrodes on said respective first and second spaced apart semiconductor source/drain regions;</p> <p>forming a protective layer on said exposed portion of said first semiconductor layer opposite said substrate, on said first and second metal source/drain electrodes opposite said substrate, and on said insulating layer opposite said gate pad;</p> <p>forming a first contact hole in said protective layer exposing a portion of one of said source/drain electrodes;</p> <p>forming a second contact hole in said protective layer and said insulating layer exposing a portion of said gate pad wherein said second contact hole exposes only a surface portion of said gate pad opposite said substrate;</p> <p>forming a transparent conductive layer on said protective layer opposite said substrate; and</p> <p>patterning said transparent conductive layer to form a pixel electrode electrically connected to said exposed portion of said source/drain electrode and to said exposed portion of said gate pad.</p>
<p>2. (New) A method according to claim 1 wherein said first metal layer comprises a material chosen from the group consisting of aluminum and an aluminum alloy.</p>
<p>4. (Currently Amended) A method according to claim 1 wherein said pixel electrode covers said exposed surface portion of said gate pad and extends onto said protective layer adjacent said second contact hole.</p>
<p>5. A method according to claim 1 wherein said step of forming said semiconductor layer comprises forming a semiconductor layer portion on said insulating layer opposite said pad area of said substrate so that said semiconductor layer portion is adjacent said second contact hole.</p>
<p>6. A method according to claim 6 wherein said step of forming said metal source/drain electrodes comprises forming a metal layer portion on said insulating layer opposite said pad area of said substrate so that said metal layer portion is adjacent said second contact hole.</p>
<p>14. A method for forming a liquid crystal display, said method comprising the steps of:</p> <p>forming a first metal layer on a substrate;</p> <p>patterning said first metal layer to provide a gate electrode on a TFT area of said substrate and to provide a gate pad on a pad area of said substrate;</p> <p>forming an insulating layer on said gate electrode and on said gate pad;</p>

<p>forming a patterned semiconductor layer on said insulating layer opposite said gate electrode and opposite said gate pad; forming a second patterned metal layer on said semiconductor layer opposite said insulating layer; forming a transparent conductive layer on said second patterned metal layer and on said insulating layer opposite said substrate; and patterning said transparent conductive layer, said second patterned metal layer, and said patterned semiconductor layer to provide a data line, metal source/drain electrodes, and a pixel electrode.</p>
<p>15. A method according to claim 14 further comprising the steps of: forming a protective layer on said substrate covering said data line, said source/drain electrodes, and said pixel electrode; and patterning said protective layer to expose portions of said pixel electrode.</p>
<p>16. A method according to claim 15 wherein said step of patterning said protective layer comprises forming a black photoresist mask, and wherein said black photoresist mask is maintained on said protective layer thereby providing a black matrix.</p>
<p>17. A method according to claim 14 wherein said semiconductor layer includes a first amorphous silicon layer and a second doped amorphous silicon layer on said first amorphous silicon layer opposite said substrate.</p>
<p>18. A method according to claim 17 wherein said step of patterning said semiconductor layer comprises etching a portion of said second doped amorphous silicon layer between said source/drain electrodes.</p>
<p>19. A method according to claim 14 wherein said first metal layer comprises a material selected from the group consisting of Aluminum, an Aluminum alloy, and a refractory metal.</p>
<p>20. A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal, and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy.</p>
<p>21. A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal on said substrate and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said first sub-layer opposite said substrate.</p>
<p>22. A method according to claim 21 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and Tantalum (Ta).</p>
<p>23. A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said substrate and a second sub-layer comprising a refractory metal on said first sub-layer opposite said substrate.</p>
<p>24. A method according to claim 23 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and Tantalum (Ta).</p>
<p>25. A method according to claim 14 further comprising the step of removing a portion of said second sub-layer from said gate pad.</p>

3. A method according to claim 99 wherein said second metal layer comprises a refractory metal.
8. (Original) A method according to claim 7 wherein said metal.
9. A method according to claim 7 wherein said second metal layer comprises a material chosen from the group consisting of Aluminum and an Aluminum alloy.
10. A method according to claim 7 wherein said pixel electrode covers said exposed surface portion of said gate pad and said substrate adjacent said gate pad, and wherein said pixel electrode extends onto said protective layer adjacent said second contact hole.
11. A method according to claim 7 wherein said step of forming said semiconductor layer comprises forming a semiconductor layer portion on said insulating layer opposite said pad area of said substrate so that said semiconductor layer portion is adjacent said second contact hole. 12 (Currently Amended). A method according to claim 7 wherein said step of forming said metal source/drain electrodes comprises forming a metal layer portion on said insulating layer opposite said pad area of said substrate so that said metal layer portion is adjacent said second contact hole.
13. A method according to claim 7 wherein said step of patterning said first and second metal layers comprises providing a plurality of interconnections on said pad area of said substrate wherein said interconnections are connected to said gate pad.

II. Claim Language Errors/Warnings

Claim	Error/Warning Message	Term At Issue	Suggested Fix
<p>1. (Original) A method for forming a liquid crystal display including a <i>thin</i> {3} film transistor, said method comprising the steps of:</p> <p>depositing a first metal layer on a substrate;</p> <p>depositing a second metal layer on said first metal layer opposite said substrate;</p> <p>patterning said first and second metal layers to provide a gate electrode on a TFT area of said substrate and to provide a gate pad on a pad area of said substrate;</p> <p>forming an insulating layer on said gate electrode and on said gate pad, and on said substrate;</p> <p>forming a semiconductor layer on said insulating layer opposite said gate electrode wherein said semiconductor layer includes a channel region opposite said gate electrode and first and second spaced apart source/drain regions separated by said channel region;</p> <p>forming first and second spaced apart metal source/drain electrodes on said respective first and second spaced apart semiconductor source/drain regions;</p> <p>forming a protective layer on said exposed portion of</p>	{1} Style warning: The claim possibly recites an empty space as a claim element.	"hole"	Claims should not recite empty spaces as claim elements.
	{2} Style warning: Claim includes possibly limiting expressions.	"only"	These phrases may unintentionally limit claim scope. Is the use of these terms necessary?
	{3} Style warning: Use of unbased comparative adjectives may render the scope of the claim indefinite.	"thin"	Rewrite/select another word to avoid ambiguity.

Claim	Error/Warning Message	Term At Issue	Suggested Fix
<p>said first semiconductor layer opposite said substrate, on said first and second metal source/drain electrodes opposite said substrate, and on said insulating layer opposite said gate pad;</p> <p>forming a first contact <i>hole {1}</i> in said protective layer exposing a portion of one of said source/drain electrodes;</p> <p>forming a second contact hole in said protective layer and said insulating layer exposing a portion of said gate pad wherein said second contact hole exposes <i>only {2}</i> a surface portion of said gate pad opposite said substrate;</p> <p>forming a transparent conductive layer on said protective layer opposite said substrate; and</p> <p>patterning said transparent conductive layer to form a pixel electrode electrically connected to said exposed portion of said source/drain electrode and to said exposed portion of said gate pad.</p>			
<p>2. (<i>New {1}</i>) A method according to claim 1 wherein said first metal layer comprises a material chosen from the <i>group consisting of {2}</i> aluminum and an aluminum alloy.</p>	<p><i>{1} Error: Claims with (New) status indicators should only appear at the end of the claim set.</i></p> <p><i>{2} Style warning: The claim may recite a Markush group. Is it intentional?</i></p>	<p>"New"</p> <p>"group consisting of"</p>	<p>Move (New) claims to the end of the claim set. See MPEP 608.01(j)</p> <p>If not intentional, claim scope may be severely limited. See MPEP 803.02.</p>

Claim	Error/Warning Message	Term At Issue	Suggested Fix
	{3} <i>Style warning:</i> Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these terms necessary?
3. A method according to claim 99 wherein said second metal layer comprises a refractory metal.	Error: Claim depends from an invalid parent.		Make sure the claim references an existing parent claim that is not cancelled.
4. (Currently Amended) A method according to claim 1 wherein said pixel electrode covers said exposed surface portion of said gate pad and extends onto said protective layer adjacent said second contact hole.	{1} Error: Claim's status identifier says that it is amended, but it is not actually amended.	"Amended"	Change the claim's status identifier to the one that does not indicate a current amendment, such as (Previously Presented).
	{2} <i>Style warning:</i> The claim possibly recites an empty space as a claim element.	"hole"	Claims should not recite empty spaces as claim elements.
5. A method according to claim 1 wherein said step of forming said semiconductor layer comprises forming a semiconductor layer portion on said insulating layer opposite said pad area of said substrate so that said semiconductor layer portion is adjacent said second contact hole.	Error: Either the claim or its parent is missing a status indicator.		If the claim has a status identifier, so should its parent (and vise-versa).
	{1} <i>Style warning:</i> The claim possibly recites an empty space as a claim element.	"hole"	Claims should not recite empty spaces as claim elements.

Claim	Error/Warning Message	Term At Issue	Suggested Fix
6. A method according to claim 6 wherein said step of forming said metal source/drain electrodes comprises forming a metal layer portion on said insulating layer opposite said pad area of said substrate so that said metal layer portion is adjacent said second contact hole.	Error: Claim cannot depend from itself.		Make sure the claim references an existing parent claim that is not cancelled.
	{1} Style warning: The claim possibly recites an empty space as a claim element.	"hole"	Claims should not recite empty spaces as claim elements.
8. (Original) A method according to claim 7 wherein said first metal layer comprises a refractory metal.	Error: Claim number is out of sequence.		Make sure claims are numbered sequentially. See MPEP 608.01(j)
	Error: Claim depends from an invalid parent.		Make sure the claim references an existing parent claim that is not cancelled.
	{1} Error: Claim is amended, but its status identifier does not reflect the amendment.	"Original"	Change the claim's status identifier to the one that indicates a current amendment, such as (Currently Amended).
9. A method according to claim 7 wherein said second metal layer comprises a material chosen from the group consisting of Aluminum and an Aluminum alloy.	Error: Claim depends from an invalid parent.		Make sure the claim references an existing parent claim that is not cancelled.
	{1} Style warning: The claim may recite a Markush group. Is it intentional?	"group consisting of"	If not intentional, claim scope may be severely limited. See MPEP 803.02.
	{2} Style warning: Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these

Claim	Error/Warning Message	Term At Issue	Suggested Fix
			terms necessary?
10. A method according to claim 7 wherein said pixel electrode covers said exposed surface portion of said gate pad and said substrate adjacent said gate pad, and wherein said pixel electrode extends onto said protective layer adjacent said second contact hole.	Error: Claim depends from an invalid parent.		Make sure the claim references an existing parent claim that is not cancelled.
	{ 1 } Style warning: The claim possibly recites an empty space as a claim element.	"hole"	Claims should not recite empty spaces as claim elements.
11. A method according to claim 7 wherein said step of forming said semiconductor layer comprises forming a semiconductor layer portion on said insulating layer opposite said pad area of said substrate so that said semiconductor layer portion is adjacent said second contact hole. 12 (Currently Amended). A method according to claim 7 wherein said step of forming said metal source/drain electrodes comprises forming a metal layer portion on said insulating layer opposite said pad area of said substrate so that said metal layer portion is adjacent said second contact hole.	Error: Claim depends from an invalid parent.		Make sure the claim references an existing parent claim that is not cancelled.
	{ 1 } Style warning: The claim possibly recites an empty space as a claim element.	"hole"	Claims should not recite empty spaces as claim elements.
13. A method according to claim 7 wherein said step of patterning said first and second metal layers comprises providing a plurality of interconnections on said pad area of said substrate wherein said interconnections are connected to said gate pad.	Error: Claim number is out of sequence.		Make sure claims are numbered sequentially. See MPEP 608.01(j)
	Error: Claim depends from an invalid parent.		Make sure the claim references an existing parent

Claim	Error/Warning Message	Term At Issue	Suggested Fix
			claim that is not cancelled.
19. A method according to claim 14 wherein said first metal layer comprises a material selected from the group consisting of Aluminum, an Aluminum alloy, and a refractory metal.	{1} <i>Style warning:</i> The claim may recite a Markush group. Is it intentional?	"group consisting of"	If not intentional, claim scope may be severely limited. See MPEP 803.02.
	{2} <i>Style warning:</i> Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these terms necessary?
20. A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal, and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy.	{1} <i>Style warning:</i> The claim may recite a Markush group. Is it intentional?	"group consisting of"	If not intentional, claim scope may be severely limited. See MPEP 803.02.
	{2} <i>Style warning:</i> Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these terms necessary?
21. A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal on said substrate and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said first sub-layer opposite said substrate.	{1} <i>Style warning:</i> The claim may recite a Markush group. Is it intentional?	"group consisting of"	If not intentional, claim scope may be severely limited. See MPEP 803.02.
	{2} <i>Style warning:</i> Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these

Claim	Error/Warning Message	Term At Issue	Suggested Fix
			terms necessary?
22. A method according to claim 21 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and Tantalum (Ta).	{1} <i>Style warning:</i> The claim may recite a Markush group. Is it intentional?	"group consisting of"	If not intentional, claim scope may be severely limited. See MPEP 803.02.
	{2} <i>Style warning:</i> Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these terms necessary?
23. A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said substrate and a second sub-layer comprising a refractory metal on said first sub-layer opposite said substrate.	{1} <i>Style warning:</i> The claim may recite a Markush group. Is it intentional?	"group consisting of"	If not intentional, claim scope may be severely limited. See MPEP 803.02.
	{2} <i>Style warning:</i> Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these terms necessary?
24. A method according to claim 23 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and Tantalum (Ta).	{1} <i>Style warning:</i> The claim may recite a Markush group. Is it intentional?	"group consisting of"	If not intentional, claim scope may be severely limited. See MPEP 803.02.
	{2} <i>Style warning:</i> Claim includes possibly limiting expressions.	"consisting"	These phrases may unintentionally limit claim scope. Is the use of these terms necessary?

Claim	Error/Warning Message	Term At Issue	Suggested Fix

III. Antecedents Errors/Warnings³

Claim	Error/Warning
<p>1. (Original) A method for forming a liquid crystal display including a thin film transistor, said method comprising the steps of:</p> <p>depositing a first metal layer on a substrate;</p> <p>depositing a second metal layer on said first metal layer opposite said substrate;</p> <p>patterning said first and second metal layers to provide a gate electrode on a TFT area of said substrate and to provide a gate pad on a pad area of said substrate;</p> <p>forming an insulating layer on said gate electrode and on said gate pad, and on said substrate;</p> <p>forming a semiconductor layer on said insulating layer opposite said gate electrode wherein said semiconductor layer includes a channel region opposite said gate electrode and first and second spaced apart source/drain regions separated by said channel region;</p> <p>forming first and second spaced apart metal source/drain electrodes on said respective first and second spaced apart semiconductor source/drain regions;</p> <p>forming a protective layer on <i>said exposed portion{1}</i> of <i>said first semiconductor layer{2}</i> opposite said substrate, on <i>said first and second metal source/drain electrode{3}{4}</i>s opposite said substrate, and on said insulating layer opposite said gate pad;</p>	<p>{1} No antecedent: "said exposed portion."</p>
	<p>{2} No antecedent: "said first semiconductor layer."</p>
	<p>{3} Double-check: "said first metal source / drain electrode." Is "first spaced apart metal source / drain electrode" in claim 1 the proper antecedent reference for this term?</p>
	<p>{4} Double-check: "said second metal source / drain electrode." Is "second spaced apart metal source / drain electrode" in claim 1 the proper antecedent reference for this term?</p>
	<p>{5} Double-check: "said source / drain electrodes." Is "first spaced apart metal source / drain electrode" in claim 1 the proper antecedent reference for this term?</p>
	<p>{6} Ambiguous: "a portion." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p>
	<p>{7} Double-check: "said source / drain electrode." Is "first spaced apart metal source / drain electrode" in claim 1 the proper antecedent reference for this term?</p>

³ Deleted (i.e., stricken-through) claim text, if any, is not shown.

Claim	Error/Warning
<p>forming a first contact hole in said protective layer exposing <i>a portion{6}</i> of one of <i>said source/drain electrodes{5}</i>;</p> <p>forming a second contact hole in said protective layer and said insulating layer exposing <i>a portion{6}</i> of said gate pad wherein said second contact hole exposes only a surface portion of said gate pad opposite said substrate;</p> <p>forming a transparent conductive layer on said protective layer opposite said substrate; and</p> <p>patterning said transparent conductive layer to form a pixel electrode electrically connected to said exposed portion of <i>said source/drain electrode{7}</i> and to said exposed portion of said gate pad.</p>	
<p>2. (New) <i>A method</i> according to claim 1 wherein said first metal layer comprises a material chosen from the group consisting of aluminum and an aluminum alloy.</p>	<p><i>Ambiguous:</i> "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p>
<p>3. A method according to claim 99 wherein <i>said second metal layer</i> comprises a refractory metal.</p>	<p><i>No antecedent:</i> "said second metal layer."</p>
<p>4. (Currently Amended) <i>A method{1}</i> according to claim 1 wherein <i>said pixel electrode covers{2}</i> <i>said exposed surface portion{3}</i> of said gate pad and extends onto said protective layer adjacent said second contact hole.</p>	<p>{1} <i>Ambiguous:</i> "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p> <p>{2} <i>No antecedent:</i> "said pixel electrode covers."</p> <p>{3} <i>Double-check:</i> "said exposed surface portion."</p>

Claim	Error/Warning
	Is "exposes only a surface portion" in claim 1 the proper antecedent reference for this term?
5. <i>A method</i> according to claim 1 wherein said step of forming said semiconductor layer comprises forming a semiconductor layer portion on said insulating layer opposite said pad area of said substrate so that said semiconductor layer portion is adjacent said second contact hole.	<i>Ambiguous:</i> "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.
6. A method according to claim 6 wherein said step of forming <i>said metal source/drain electrodes{1}</i> comprises forming a metal layer portion on <i>said insulating layer{2}</i> opposite <i>said pad area{3}</i> of <i>said substrate{4}</i> so that said metal layer portion is adjacent <i>said second contact hole{5}</i> .	{1} <i>No antecedent:</i> "said metal source / drain electrodes." {2} <i>No antecedent:</i> "said insulating layer." {3} <i>No antecedent:</i> "said pad area." {4} <i>No antecedent:</i> "said substrate." {5} <i>No antecedent:</i> "said second contact hole."
8. (Original) A method according to claim 7 wherein <i>said metal</i> .	<i>No antecedent:</i> "said metal."
9. A method according to claim 7 wherein <i>said second metal layer</i> comprises a material chosen from the group consisting of Aluminum and an Aluminum alloy.	<i>No antecedent:</i> "said second metal layer."
10. A method according to claim 7 wherein <i>said pixel electrode covers{1}</i> <i>said exposed surface portion{2}</i> of <i>said gate pad{3}</i> and <i>said substrate{4}</i> adjacent said gate pad, and wherein <i>said pixel electrode{5}</i> extends onto <i>said protective layer{6}</i> adjacent <i>said second contact hole{7}</i> .	{1} <i>No antecedent:</i> "said pixel electrode covers." {2} <i>No antecedent:</i> "said exposed surface portion." {3} <i>No antecedent:</i> "said gate pad." {4} <i>No antecedent:</i> "said substrate." {5} <i>No antecedent:</i> "said pixel electrode."

Claim	Error/Warning
	<p>{6} No antecedent: "said protective layer."</p> <p>{7} No antecedent: "said second contact hole."</p>
<p>11. <i>A method</i>{6} according to claim 7 wherein said step of forming <i>said semiconductor layer</i>{1} comprises forming a semiconductor layer portion on <i>said insulating layer</i>{2} opposite <i>said pad area</i>{3} of <i>said substrate</i>{4} so that said semiconductor layer portion is adjacent <i>said second contact hole</i>{5}.</p> <p>12 (Currently Amended). <i>A method</i>{6} according to claim 7 wherein said step of forming <i>said metal source/drain electrodes</i>{7} comprises forming a metal layer portion on said insulating layer opposite said pad area of said substrate so that said metal layer portion is adjacent said second contact hole.</p>	<p>{1} No antecedent: "said semiconductor layer."</p> <p>{2} No antecedent: "said insulating layer."</p> <p>{3} No antecedent: "said pad area."</p> <p>{4} No antecedent: "said substrate."</p> <p>{5} No antecedent: "said second contact hole."</p> <p>{6} Ambiguous: "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p> <p>{7} No antecedent: "said metal source / drain electrodes."</p>
<p>13. A method according to claim 7 wherein said step of patterning <i>said first and second metal layer</i>{1}{2}s comprises providing a plurality of interconnections on <i>said pad area</i>{3} of <i>said substrate</i>{4} wherein said interconnections are connected to <i>said gate pad</i>{5}.</p>	<p>{1} No antecedent: "said first metal layer."</p> <p>{2} No antecedent: "said second metal layer."</p> <p>{3} No antecedent: "said pad area."</p> <p>{4} No antecedent: "said substrate."</p> <p>{5} No antecedent: "said gate pad."</p>
<p>14. A method for forming a liquid crystal display, said method comprising the steps of:</p> <p>forming a first metal layer on a substrate;</p> <p>patterning said first metal layer to provide a gate electrode on a TFT area of said substrate and to provide a gate pad on a pad area of said substrate;</p> <p>forming an insulating layer on said gate electrode and on said gate pad;</p>	<p>Double-check: "said semiconductor layer." Is "a patterned semiconductor layer" in claim 14 the proper antecedent reference for this term?</p>

Claim	Error/Warning
<p>forming a patterned semiconductor layer on said insulating layer opposite said gate electrode and opposite said gate pad;</p> <p>forming a second patterned metal layer on <i>said semiconductor layer</i> opposite said insulating layer;</p> <p>forming a transparent conductive layer on said second patterned metal layer and on said insulating layer opposite said substrate; and</p> <p>patterning said transparent conductive layer, said second patterned metal layer, and said patterned semiconductor layer to provide a data line, metal source/drain electrodes, and a pixel electrode.</p>	
<p>15. <i>A method{1}</i> according to claim 14 further comprising the steps of:</p> <p>forming a protective layer on said substrate covering said data line, <i>said source/drain electrodes{2}</i>, and said pixel electrode; and</p> <p>patterning said protective layer to expose portions of said pixel electrode.</p>	<p>{1} Ambiguous: "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p> <p>{2} Double-check: "said source / drain electrodes." Is "metal source / drain electrodes" in claim 14 the proper antecedent reference for this term?</p>
<p>16. <i>A method</i> according to claim 15 wherein said step of patterning said protective layer comprises forming a black photoresist mask, and wherein said black photoresist mask is maintained on said protective layer thereby providing a black matrix.</p>	<p>Ambiguous: "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p>
<p>17. <i>A method{1}</i> according to claim 14 wherein <i>said semiconductor layer{2}</i></p>	<p>{1} Ambiguous: "a method." Make sure that the use</p>

Claim	Error/Warning
<p>includes a first amorphous silicon layer and a second doped amorphous silicon layer on said first amorphous silicon layer opposite said substrate.</p>	<p>of multiple instances of this term with an indefinite article does not create ambiguity.</p> <p>{2} Double-check: "said semiconductor layer." Is "a patterned semiconductor layer" in claim 14 the proper antecedent reference for this term?</p>
<p>18. <i>A method</i>{1} according to claim 17 wherein said step of patterning <i>said semiconductor layer</i>{2} comprises etching a portion of said second doped amorphous silicon layer between <i>said source/drain electrodes</i>{3}.</p>	<p>{1} Ambiguous: "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p> <p>{2} Double-check: "said semiconductor layer." Is "a patterned semiconductor layer" in claim 14 the proper antecedent reference for this term?</p> <p>{3} Double-check: "said source / drain electrodes." Is "metal source / drain electrodes" in claim 14 the proper antecedent reference for this term?</p>
<p>19. <i>A method</i> according to claim 14 wherein said first metal layer comprises a material selected from the group consisting of Aluminum, an Aluminum alloy, and a refractory metal.</p>	<p>Ambiguous: "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p>
<p>20. <i>A method</i> according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal, and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy.</p>	<p>Ambiguous: "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p>
<p>21. <i>A method</i> according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal on said substrate and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an</p>	<p>Ambiguous: "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p>

Claim	Error/Warning
Aluminum alloy on said first sub-layer opposite said substrate.	
22. <i>A method</i> according to claim 21 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and Tantalum (Ta).	<i>Ambiguous:</i> "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.
23. <i>A method</i> according to claim 14 wherein said first metal layer includes a first sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said substrate and a second sub-layer comprising a refractory metal on said first sub-layer opposite said substrate.	<i>Ambiguous:</i> "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.
24. <i>A method</i> according to claim 23 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and Tantalum (Ta).	<i>Ambiguous:</i> "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.
25. <i>A method{1}</i> according to claim 14 further comprising the step of removing a portion of <i>said second sub-layer{2}</i> from said gate pad.	<p><i>{1} Ambiguous:</i> "a method." Make sure that the use of multiple instances of this term with an indefinite article does not create ambiguity.</p> <p><i>{2} No antecedent:</i> "said second sub - layer."</p>

IV. **Claim Terms without Explicit Support in the Specification**

Claim	Term Without Support
13. A method according to claim 7 wherein said step of patterning said first and second metal layers comprises providing a plurality of interconnections on said pad area of said substrate wherein said interconnections are connected to said gate pad.	interconnections
10. A method according to claim 7 wherein said <u>pixel electrode covers</u> said exposed surface portion of said gate pad and said substrate adjacent said gate pad, and wherein said pixel electrode extends onto said protective layer adjacent said second contact hole.	pixel electrode covers
4. (Currently Amended) A method according to claim 1 wherein said <u>pixel electrode covers</u> said exposed surface portion of said gate pad and extends onto said protective layer adjacent said second contact hole.	pixel electrode covers
16. A method according to claim 15 wherein said step of patterning said protective layer comprises forming a <u>black photoresist mask</u> , and wherein said black photoresist mask is maintained on said protective layer thereby providing a <u>black matrix</u> .	black photoresist mask black matrix
20. A method according to claim 14 wherein said first metal layer includes a first <u>sub-layer</u> comprising a refractory metal, and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy.	sub-layer
21. A method according to claim 14 wherein said first metal layer includes a first <u>sub-layer</u> comprising a refractory metal on said substrate and a second sub-layer comprising a material chosen from the group consisting	sub-layer

Claim	Term Without Support
of Aluminum and an Aluminum alloy on said first sub-layer opposite said substrate.	
23. A method according to claim 14 wherein said first metal layer includes a first <u>sub-layer</u> comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said substrate and a second sub-layer comprising a refractory metal on said first sub-layer opposite said substrate.	sub-layer
25. A method according to claim 14 further comprising the step of removing a portion of said second <u>sub-layer</u> from said gate pad.	sub-layer
22. A method according to claim 21 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and <u>Tantalum</u> (Ta).	tantalum
24. A method according to claim 23 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and <u>Tantalum</u> (Ta).	tantalum

V. Inconsistent Part Names/Numbers

Note: terms completely in red are more likely to be incorrectly named or numbered. With partially inconsistent names, mismatched sections are colored in orange.

Part Number	Consistently Used Part Name [# of occurrences]	Inconsistently Named/Numbered Part [# of occurrences]	Citations [Page/Line # in the document]
3	source lines	data lines	Also, a plurality of data lines 3 are provided lengthwise, and a respective data pad 4 is provided ... [Page 12, line 31.]
10	substrate	transparent line	A metal layer is forming by depositing aluminum (Al) on a transparent line 10 , and this metal layer is patterned using a first photolithography step to ... [Page 5, line 27.]
11	gate electrode	gate line	An insulating layer 15, such as a nitride layer, is deposited on the substrate 10 including the gate line 11 and the anodic oxide layer 13. [Page 5, line 34.]
21a	drain electrodes	source electrode	A source electrode 21a and a drain electrode 21b are formed on the TFT are of the ... [Page 6, line 4.]
32	first metal layer	second metal layers	2 formed on the TFT and pad areas of the substrate have a double layer structure formed by sequentially depositing first and second metal layers 32 and 34. [Page 7, line 9.]
		aluminum alloy layer	As shown, this TFT-LCD includes a substrate 30, an aluminum alloy layer 32 , a refractory metal capping layer 34, an insulating layer 36 ... [Page 7, line 3.]
34	second metal layer	refractory metal capping layer	As shown, this TFT-LCD includes a substrate 30, an aluminum alloy layer 32, a refractory metal capping layer 34 , an insulating layer 36 which can be a

Part Number	Consistently Used Part Name [# of occurrences]	Inconsistently Named/Numbered Part [# of occurrences]	Citations [Page/Line # in the document]
			nitride layer... [Page 7, line 4.]
51	first metal layer	second metal layers	On the pad area of the substrate, the gate electrode (including the first and second metal layers 51 and 53) and the pad electrode 61c are connected by the ... [Page 7, line 39.]
70	substrate	transparent substrate	7A, a first metal layer 72 is formed by depositing Al or an Al alloy on a transparent substrate 70 . [Page 13, line 17.]
72	first metal layer	layers	This ITO layer is patterned using fifth photolithography and etch steps to provide a pixel electrode 86 connected to the gate pad including layers 72 and 74 on the pad area of the substrate and connected to the drain ... [Page 14, line 21.]
74	second metal layer	layers	This ITO layer is patterned using fifth photolithography and etch steps to provide a pixel electrode 86 connected to the gate pad including layers 72 and 74 on the pad area of the substrate and connected to the drain ... [Page 14, line 21.]
78	amorphous silicon layer	layers [2]	7C, a third metal layer is formed by depositing a metal such as chromium (Cr), molybdenum (Mo), or titanium (Ti) on the patterned semiconductor layer including layers 78 and 80 opposite the substrate 70. [Page 13, line 31.] Next, after forming a semiconductor layer comprising an amorphous silicon layer 78 and a doped amorphous silicon layer on the insulating layer 76, a patterned semiconductor layer including layers 78 and 80 is formed on the TFT area of the substrate by performing a ... [Page 13, line 27.]
80	layers	doped amorphous silicon	At this time, the doped amorphous silicon layer 80 is also etched to expose a

Part Number	Consistently Used Part Name [# of occurrences]	Inconsistently Named/Numbered Part [# of occurrences]	Citations [Page/Line # in the document]
		layer	portion of the amorphous silicon ... [Page 13, line 34.]
112	pixel electrode	gate pad	At this time, a portion of the protective layer 124 on the pixel electrode 112 is etched and the protective layer 124 and insulating layer 114 on the gate pad 112 are partially etched so that a portion of the pad electrode is exposed... [Page 15, line 26.]

VI. Inconsistent Part Numbers in Figures

Part Number	Found in Figures?	Found in Specification?
1	No	Yes
2	No	Yes
21a	No	Yes
21b	No	Yes
21c	No	Yes
2b	No	Yes
3	No	Yes
4	No	Yes
5	No	Yes
6	No	Yes
10	No	Yes
11	No	Yes
13	No	Yes
15	No	Yes
17	No	Yes
19	No	Yes
22	No	Yes
23	No	Yes
25	No	Yes
30	No	Yes
32	No	Yes
34	No	Yes
36	No	Yes
38	No	Yes
40a	No	Yes
42a	No	Yes
42b	No	Yes

44	No	Yes
46	No	Yes
50	No	Yes
53	No	Yes
55	No	Yes
57	No	Yes
59	No	Yes
61a	No	Yes
61b	No	Yes
61c	No	Yes
63	No	Yes
67	No	Yes
72	No	Yes
74	No	Yes
76	No	Yes
78	No	Yes
82a	No	Yes
82b	No	Yes
84	No	Yes
86	No	Yes
88	No	Yes
110	No	Yes
114	No	Yes
124	No	Yes
125	No	Yes
222	Yes	No
555	Yes [multiple appearances]	No
890a	Yes [multiple appearances]	No

VII. **Inconsistent Acronyms**

Acronym	Error Message
FT	Acronym is not defined in text.
TFT	Acronym is used before being defined.

VIII. Document Language Errors/Warnings

Error/Suggested Fix	Citations [Page/Line # in the document]
<p>Avoid using vague and relative terms. Use of vague and relative terms in the specification can potentially render patent invalid and unenforceable under 35 U.S.C. 112.</p>	<p>Because a thin film transistor (TFT) may be thinner than a conventional transistor, methods used to manufacture a thin film transistor may be more complicated ... [Page 5, line 16.]</p> <p>A method for manufacturing a conventional liquid crystal display will now be described with reference to FIGS. [Page 5, line 25.]</p> <p>In the drawings and specification, there have been disclosed typical preferred embodiments of the invention and, although specific terms are employed, they ... [Page 15, line 29.]</p>
<p>Document text includes potentially limiting language. Make sure that limiting terms are used correctly, to avoid the potential infringer trying to limit the scope of the patent based on the statements in the specification.</p>	<p>forming a second contact hole in said protective layer and said insulating layer exposing a portion of said gate pad wherein said second contact hole exposes only a surface portion of said gate pad opposite said substrate; [Page 2, line 5.]</p> <p>A first contact hole is formed in the protective layer exposing a portion of one of the source/drain electrodes, and a second contact hole is formed in the protective layer and the insulating layer exposing a portion of the gate pad wherein the second contact hole exposes only a surface portion of the gate pad opposite the substrate. [Page 9, line 27.]</p> <p>Accordingly, etching of the substrate is reduced, and the aluminum or aluminum alloy layer is exposed only at a portion C. [Page 15, line 21.]</p> <p>In the drawings and specification, there have been disclosed typical preferred embodiments of the invention and, although specific terms are employed, they are used in a generic and descriptive sense only and not for purposes of limitation, the scope of the invention being set ... [Page 15, line 31.]</p> <p>A first contact hole is formed in the protective layer exposing a portion of one of the source/drain electrodes, and a second contact hole is formed in the</p>

Error/Suggested Fix	Citations [Page/Line # in the document]
	<p>protective layer and the insulating layer exposing a portion of the gate pad wherein the second contact hole exposes only a surface portion of the gate pad opposite the substrate. [Page 16, line 9.]</p> <p>(New) A method according to claim 1 wherein said first metal layer comprises a material chosen from the group consisting of aluminum and an aluminum alloy. [Page 2, line 14.]</p> <p>A method according to claim 7 wherein said second metal layer comprises a material chosen from the group consisting of Aluminum and an Aluminum alloy. [Page 2, line 34.]</p> <p>A method according to claim 14 wherein said first metal layer comprises a material selected from the group consisting of Aluminum, an Aluminum alloy, and a refractory metal. [Page 4, line 6.]</p> <p>A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal, and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy. [Page 4, line 10.]</p> <p>A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a refractory metal on said substrate and a second sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said first sub-layer opposite said ... [Page 4, line 14.]</p> <p>A method according to claim 21 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and ... [Page 4, line 18.]</p> <p>A method according to claim 14 wherein said first metal layer includes a first sub-layer comprising a material chosen from the group consisting of Aluminum and an Aluminum alloy on said substrate and a second sub-... [Page 4, line 21.]</p>

Error/Suggested Fix	Citations [Page/Line # in the document]
	<p>A method according to claim 23 wherein said refractory metal selected from the group consisting of chromium (Cr), Molybdenum (Mo), Titanium (Ti), and ... [Page 4, line 26.]</p> <p>In addition, the number of photolithography steps can be reduced by simultaneously etching both the insulating layer 36 and the protective layer 44. [Page 7, line 24.]</p> <p>As shown, the gate electrodes formed on the TFT and pad areas of the substrate each have a double-layer structure formed by sequentially depositing a first metal layer ... [Page 7, line 34.]</p> <p>5, a plurality of gate lines 1 are provided laterally, and a respective gate pad 2 is provided at the end of each of the gate lines 1. [Page 12, line 30.]</p> <p>A thin film transistor 5 and a pixel electrode 6 are connected to each of the gate lines 1. [Page 12, line 31.]</p> <p>Also, a plurality of data lines 3 are provided lengthwise, and a respective data pad 4 is provided at the end of each of the source lines 3. [Page 12, line 32.]</p> <p>The present invention will now be described more fully hereinafter with reference to the accompanying drawings, in which preferred embodiments of the invention are shown. [Page 12, line 19.]</p> <p>This invention may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein; rather, ... [Page 12, line 20.]</p> <p>7B, a nitride layer is deposited on the entire surface of the substrate 70 where the gate electrode and pad electrode are formed... [Page 13, line 23.]</p> <p>7D, a protective layer is formed by depositing a nitride layer on the entire surface of the substrate including the source electrode 82a and the drain electrode 82b... [Page 14, line 1.]</p>

Error/Suggested Fix	Citations [Page/Line # in the document]
	<p>7E, an ITO layer, which is a transparent conductive layer, is formed on the entire surface of the substrate where the protective layer 84 is formed. [Page 14, line 18.]</p> <p>18A and 18B, a protective layer 124 is formed by depositing an insulating layer such as a nitride layer on the entire surface of the substrate 110, and then performing a fourth photolithography step on ... [Page 15, line 23.]</p> <p>According to the aforementioned first embodiment of the present invention, the number of required masks can be reduced and aluminum hillock growth can be reduced by forming a ... [Page 14, line 25.]</p> <p>Therefore, the step coverage of the ITO layer for the pixel electrode can be improved without a separate photolithography step. [Page 15, line 13.]</p>
<p>Document text includes excluding phrases. Excluding phrases in the specification may be used to limit the scope of your claims. Review, to ensure that potential infringers do not try to limit the scope of the patent based on the statements in the specification.</p>	<p>In addition, the protective layer 84 and the insulating layer 76 are patterned with a predetermined distance d set for preventing a portion where the protective layer 84 and insulating layer 76 are opened from ... [Page 14, line 12.]</p> <p>Therefore, the step coverage of the ITO layer for the pixel electrode can be improved without a separate photolithography step. [Page 15, line 13.]</p>
<p>Document text includes contrasting phrases. Contrasting phrases may be used to limit the scope of your claims. Review, to ensure that potential infringers do not try to limit the scope of the patent based on the statements in the specification.</p>	<p>If Al and ITO are in direct contact, however, the ITO may dissolve in a developing solution due to a battery effect caused ... [Page 8, line 19.]</p> <p>This invention may, however, be embodied in many different forms and should not be construed as limited to ... [Page 12, line 20.]</p> <p>It is still another object of the present invention to provide methods for forming liquid crystal displays ... [Page 9, line 8.]</p>
<p>Do not use words such as 'invention' or 'embodiment' . At least in the U.S., there exists legal precedent for using patentee's</p>	<p>FIELD OF THE INVENTION [Page 4, line 35.]</p>

Error/Suggested Fix	Citations [Page/Line # in the document]
<p>statements regarding the 'invention' to limit the claim scope during litigation. Avoid any direct characterizations of 'invention' or 'preferred embodiments', if possible.</p>	<p>The present <u>invention</u> relates to the field of microelectronics and more particularly to methods for forming liquid ... [Page 4, line 37.]</p> <p><u>BACKGROUND OF THE INVENTION</u> [Page 4, line 40.]</p> <p><u>SUMMARY OF THE INVENTION</u> [Page 8, line 37.]</p> <p>It is therefore an object of the present <u>invention</u> to provide improved methods for forming liquid crystal displays. [Page 9, line 2.]</p> <p>It is another object of the present <u>invention</u> to provide methods for forming liquid crystal displays having improved reliability. [Page 9, line 5.]</p> <p>It is still another object of the present <u>invention</u> to provide methods for forming liquid crystal displays using a reduced number of photolithography ... [Page 9, line 8.]</p> <p>These and other objects are provided according to the present <u>invention</u> by methods including the steps of depositing a first metal layer on a substrate ... [Page 9, line 11.]</p> <p>According to an alternate aspect of the present <u>invention</u>, a method for forming a liquid crystal display includes the steps of depositing a ... [Page 10, line 5.]</p> <p>According to another alternate aspect of the present <u>invention</u>, a method for forming a liquid crystal display includes the steps of forming a ... [Page 10, line 26.]</p> <p>The methods of the present <u>invention</u> thus allow the manufacture of liquid crystal displays with a reduced number of photolithography ... [Page 10, line 37.]</p> <p>5 is a plan view illustrating an LCD formed using a method according to the present <u>invention</u>. [Page 11, line 13.]</p>

Error/Suggested Fix	Citations [Page/Line # in the document]
	<p>6 is a schematic plan view illustrating a pad area for forming an LCD using a method according to a first <u>embodiment</u> of the present <u>invention</u>. [Page 11, line 16.]</p> <p>7A through 7E are cross sectional views illustrating steps of a method for forming an LCD according to the first <u>embodiment</u> of the present <u>invention</u>. [Page 11, line 19.]</p> <p>8 is a schematic plan view illustrating a method for forming an LCD according to a second <u>embodiment</u> of the present <u>invention</u>. [Page 11, line 22.]</p> <p>9 is a cross sectional view illustrating an LCD formed using a method according to the second <u>embodiment</u> of the present <u>invention</u>. [Page 11, line 25.]</p> <p>10 is a plan view illustrating a method for forming an LCD according to a third <u>embodiment</u> of the present <u>invention</u>. [Page 11, line 28.]</p> <p>11A through 11E are cross sectional views illustrating steps of a method for forming an LCD according to the second <u>embodiment</u> of the present <u>invention</u>. [Page 12, line 2.]</p> <p>12 through 14 are plan views illustrating methods for forming an LCD according to fourth, fifth, and sixth embodiments of the present <u>invention</u>. [Page 12, line 5.]</p> <p>19 is a cross sectional view illustrating a method for forming an LCD according to an eighth <u>embodiment</u> of the present <u>invention</u>. [Page 12, line 8.]</p> <p>20 is a cross sectional view illustrating a method for forming an LCD according to a ninth <u>embodiment</u> of the present <u>invention</u>. [Page 12, line 11.]</p> <p>21 is a cross sectional view illustrating a method for forming an LCD</p>

Error/Suggested Fix	Citations [Page/Line # in the document]
	<p>according to a tenth <u>embodiment</u> of the present <u>invention</u>. [Page 12, line 14.]</p> <p>The present <u>invention</u> will now be described more fully hereinafter with reference to the accompanying drawings, ... [Page 12, line 18.]</p> <p>This <u>invention</u> may, however, be embodied in many different forms and should not be ... [Page 12, line 20.]</p> <p>5 is a plan view illustrating drain electrodes to a method of the present <u>invention</u>. [Page 12, line 28.]</p> <p>6 is a schematic plan view of a pad area, and this figure is used to explain a method for forming an LCD according to a first <u>embodiment</u> of the present <u>invention</u>. [Page 13, line 3.]</p> <p>7A through 7E are cross sectional views illustrating steps of a method for forming an LCD according to a first <u>embodiment</u> of the present <u>invention</u>. [Page 13, line 16.]</p> <p>According to the aforementioned first <u>embodiment</u> of the present <u>invention</u>, the number of required masks can be reduced and aluminum hillock growth can be ... [Page 14, line 24.]</p> <p>8 is a schematic plan view for illustrating an LCD formed using a method according to a second <u>embodiment</u> of the present <u>invention</u>, and FIG. [Page 14, line 35.]</p> <p>9 is a cross sectional view illustrating an LCD formed using a method according to the second <u>embodiment</u> of the present <u>invention</u>. [Page 14, line 36.]</p> <p>10 is a schematic plan view illustrating the pad area of an LCD formed by a method according to a third <u>embodiment</u> of the present <u>invention</u>. [Page 15, line 16.]</p>

Error/Suggested Fix	Citations [Page/Line # in the document]
	<p>In the drawings and specification, there have been disclosed typical preferred embodiments of the <u>invention</u> and, although specific terms are employed, they are used in a generic ... [Page 15, line 30.]</p>

